

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph bridging page 10 and page 11 with the following amended paragraph:

FIG. 4 shows a thickness of each layer in a polymeric optical device (AWG) being fabricated according to a preferred embodiment of the present invention. Referring to FIG. 4, the lower cladding layer 12 having a thickness of 11  $\mu\text{m}$  is formed on the silicon substrate 10 (~~referring to FIG. 2E~~), the core layer pattern 14a of about 6x6  $\mu\text{m}$  is formed on the lower cladding layer 12, and the upper cladding layer 18 having a thickness of about 16  $\mu\text{m}$  or more is formed on the lower cladding layer 12 in which the core layer pattern 14 is formed. At this time, the core layer pattern 14a of 6x6  $\mu\text{m}$  is formed by forming the core layer 14 having a thickness of 6  $\mu\text{m}$  on the lower cladding layer 16 and then etching it by a thickness of about 7  $\mu\text{m}$  into a shape of the etching mask, which is formed by means of the photolithography method, as described above. Here, the thickness of the core layer 14 is 6  $\mu\text{m}$ , but the etched depth of the core layer 14 is 7  $\mu\text{m}$ . It means that the lower cladding layer 12 is over-etched by about 1  $\mu\text{m}$ .

Please replace the second full paragraph on page 6 with the following amended paragraph:

FIGs. 2A to ~~2E~~ 2D are cross sectional views of processes, respectively, for explaining a method for fabricating the polymeric

optical device of FIG. 1.